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# Characterizing the LSI Yield Equation from Wafer Test Data

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**Abstract**—The results of production test on LSI wafers are analyzed to determine the parameters of the yield equation. Recognizing that a physical defect on a chip can produce several logical faults, the number of faults per defect is assumed to be a random variable with Poisson distribution. The analysis provides a relationship between the yield of the tested fraction of the chip area and the cumulative fault coverage of test patterns. The parameters of the yield equation are estimated by fitting this relation to the measured yield versus fault coverage data.

## I. INTRODUCTION

THE established approach to yield estimation of LSI chips is based upon an assumed defect-density distribution over a wafer. The yield equation, i.e., the yield versus chip area relationship, is expressed in terms of the parameters of this distribution which are estimated either from monitor wafers [1] or from a few carefully placed test chips on each wafer [2]–[4]. The monitors or test chips are designed to detect commonly known types of *physical defects*, such as opens and shorts in the layers of diffusion, polysilicon, and metal or the *parametric irregularities*. Once the distribution of defect-density is determined, the chip yield can be calculated. The parameters of yield equation not only vary from wafer-to-wafer or lot-to-lot but also undergo variations within a wafer. A continuous monitoring is, therefore, desirable.

In addition to parametric testing the wafer test also includes the functional testing of *all* the chips on the wafer. It was shown in [5] that the chip failure data thus obtained can be analyzed to estimate the *reject ratio*, that is, the fraction of bad chips passed as good by the tests. In this paper, we show that further use can be made of the same data in characterizing the yield equation. A compound model is introduced in which each physical defect is assumed to produce a random number of *logical faults*. The parameters of the model are derived from the functional test process. These test data reflect the effect of fault distribution over all the chips on a wafer instead of a few defect monitors.

## II. ANALYSIS

Let  $x$  be the random variable denoting the number of physical defects on a chip. Following Stapper [6] we will assume that  $x$  has a *negative binomial distribution* given by [7, p. 18]:

$$p_1(x) = \text{Prob}(\text{number of defects} = x) \\ = \binom{x+a-1}{x} (Ab)^x (1+Ab)^{-x-a} \quad (1)$$

where  $A$  is the chip area, and  $a \geq 0$ , and  $b > 0$  are two parameters. Further, we assume that each physical defect can produce several faults, such as stuck-at-1's, stuck-at-0's, etc. Suppose a given chip has  $x$  defects and the  $i$ th defect causes  $k_i$  faults. Then the total number of faults on the chip is

$$n = \sum_{i=1}^x k_i.$$

We assume that the random variables  $k_i$  are independent and that their values occur with probabilities given by a Poisson distribution having mean  $c$ . Then the total number of faults in the presence of  $x$  defects will have a distribution which is the  $x$ -fold convolution of identical Poisson distributions. This is known to be a Poisson distribution also [8, p. 268] with mean  $cx$ . Thus

$$p_2(n|x) = \text{Prob}(\text{number of faults} = n | x \text{ defects}) \\ = \frac{(cx)^n}{n!} e^{-cx}. \quad (2)$$

With the help of (1) and (2) we can express a *generalized distribution* [7, p. 21] for the number of faults on a chip:

$$p_3(n) = \text{Prob}(\text{number of faults} = n) \\ = \sum_{x=0}^{\infty} p_2(n/x) p_1(x). \quad (3)$$

Next, we will derive the probability generating function (p.g.f.) for  $p_3(n)$  which is defined as

$$G_3(s) \triangleq \sum_{n=0}^{\infty} p_3(n) s^n \quad (4)$$

where  $s$  is the transformation variable (see [8, p. 264]). Substituting from (3), we get,

$$G_3(s) = \sum_{n=0}^{\infty} \sum_{x=0}^{\infty} p_2(n/x) p_1(x) s^n \\ = \sum_{x=0}^{\infty} p_1(x) \sum_{n=0}^{\infty} p_2(n/x) s^n.$$

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The inner summation in the last expression represents the p.g.f. of the Poisson distribution [7, p. 14] which is  $e^{cx(s-1)}$ . Therefore,

$$\begin{aligned} G_3(s) &= \sum_{x=0}^{\infty} p_1(x) e^{cx(s-1)} \\ &= \sum_{x=0}^{\infty} p_1(x) t^x \quad \text{where } t = e^{c(s-1)} \\ &= G_1(t) \end{aligned}$$

where  $G_1$  represents the p.g.f. of the negative-binomial distribution  $p_1$ . This has the closed-form expression ([7, p. 17])

$$G_1(t) = (1 + Ab - Abt)^{-a}$$

which, upon substitution of the expression for  $t$ , yields the desired p.g.f. as

$$G_3(s) = [1 + Ab(1 - e^{c(s-1)})]^{-a}. \quad (5)$$

If  $f$  is the fault coverage expressed as a fraction of total faults, then  $1 - f$  will be the probability of a randomly selected fault remaining undetected by the tests. When the chip has  $n$  faults, the probability of none of them being detected by the tests can be approximated as  $(1 - f)^n$ . This approximation is accurate under quite general conditions as shown in [9]. Now since  $n$  is a random variable with probability density  $p_3(n)$ , the apparent yield of chips that pass the tests will be

$$y + Y_{bg}(f) = \sum_{n=0}^{\infty} p_3(n) (1 - f)^n$$

where the left-hand side simply indicates that the apparent yield is composed of the true yield  $y$  and the yield  $Y_{bg}(f)$  of bad chips tested as good. From the definition of probability generating function given by (4) the above expression is equivalent to  $G_3(1 - f)$ . Thus using (5), we get

$$y + Y_{bg}(f) = [1 + Ab(1 - e^{-cf})]^{-a}. \quad (6)$$

Obviously, for a complete fault coverage ( $f = 1$ ),  $Y_{bg}$  is zero. Thus the yield is given by

$$y = [1 + Ab(1 - e^{-c})]^{-a}. \quad (7)$$

Reject ratio, which is defined as the fraction of bad chips among those that are tested good can be computed from (6) and (7) as follows:

$$r(f) = \frac{Y_{bg}(f)}{y + Y_{bg}(f)} = 1 - \left[ \frac{1 + Ab(1 - e^{-c})}{1 + Ab(1 - e^{-cf})} \right]^{-a}. \quad (8)$$

Let  $P(f)$  represent the fraction of chips rejected by test patterns with cumulative fault-coverage  $f$ , then,

$$P(f) = 1 - y - Y_{bg}(f) = 1 - [1 + Ab(1 - e^{-cf})]^{-a}. \quad (9)$$

### III. ESTIMATION OF PARAMETERS

The wafer test data for an LSI chip was analyzed. This chip contained approximately 2700 transistors. The chip-failure data was combined with the results from fault simulation to obtain a plot of the fraction  $P(f)$  of failing chips versus the

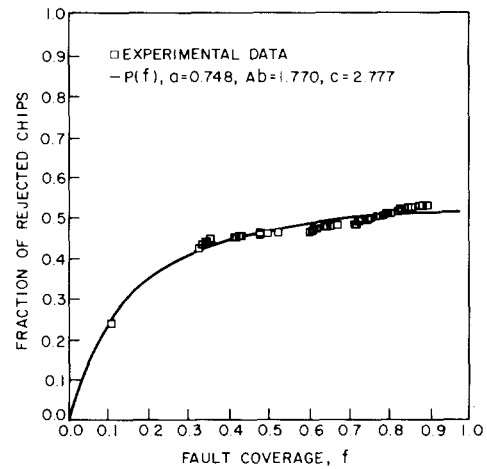


Fig. 1. Wafer-test data: Fraction of rejected chips as a function of fault coverage.

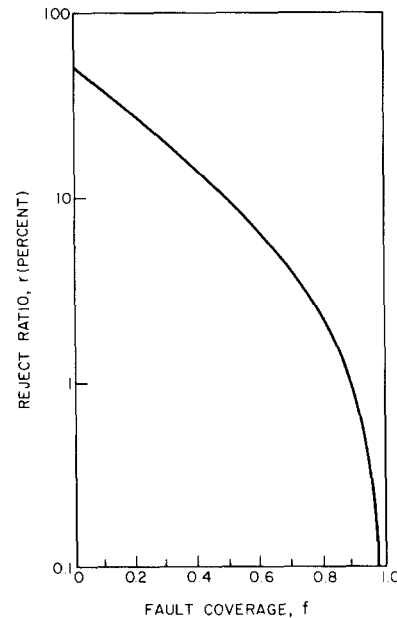


Fig. 2. Reject ratio versus fault coverage as computed from (8) using the estimated parameters  $a = 0.748$ ,  $Ab = 1.77$ , and  $c = 2.777$ .

fault coverage  $f$  (see [5] for further details of this procedure.) The resultant data are shown as the points in Fig. 1. A weighted least squares procedure was used to estimate the parameters  $a$ ,  $Ab$ , and  $c$  in (9) that best fit these data [10]. The results were as follows:

$$a = 0.748, \quad Ab = 1.770, \quad \text{and} \quad c = 2.777.$$

From (7) the yield for these values of the parameters is 48 percent which agrees closely with the expected yield for this chip. The reject ratio for the tests, which have a 90-percent fault coverage, is about one percent as computed from (8) (see Fig. 2). Also for a 0.1-percent reject ratio ( $r = 0.001$ ), about 99-percent fault coverage will be required.

### IV. YIELD AND FAULT COVERAGE

Stapper's yield equation is written as [6]

$$y = [1 + A\bar{D}(\sigma/\mu)^2]^{-(\mu/\sigma)^2} \quad (10)$$

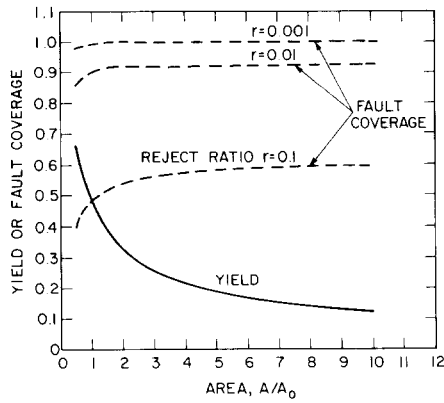


Fig. 3. Yield Equation: Yield versus area (solid curve) computed from the estimated parameters,  $a = 0.748$ ,  $A_0b = 1.77$ ,  $c = 2.777$ . The normalizing area  $A_0$  is the area of the chip of Fig. 1. The dashed curves are the computed fault coverages required for reject ratios of 10-, 1-, and 0.1-percent.

where  $\bar{D}$  is the average defect density and  $\sigma/\mu$  is the coefficient of variation of the defect density.  $A$  is the chip area. Comparing (10) and (7), we get

$$\sigma/\mu = \sqrt{1/a}$$

and

$$A\bar{D} = Ab(1 - e^{-c})a. \tag{11}$$

For the chip considered in the previous section,  $\sigma/\mu = 1.16$  and  $A\bar{D} = 1.93$ . These values are of the same order as those given in [6]. Fig. 3 shows a yield versus area curve (solid line) as computed from these values. The normalizing area  $A_0$  in this graph is the area of the chip whose test results were analyzed in the previous section.

For a given reject ratio  $r$ , (8) can be solved to give the required fault coverage,

$$f = -\frac{1}{c} \ln \left[ 1 + \frac{1 - (1 - r)^{1/a} \{1 + Ab(1 - e^{-c})\}}{Ab} \right]. \tag{12}$$

The fault coverages as computed from this formula are shown in Fig. 3 by dashed curves. It is interesting to note that as the area increases, for a given reject ratio, the required fault coverage converges to a fixed value. For example, a 1-percent reject ratio ( $r = 0.01$ ) would require about 93-percent fault coverage. These results are, of course, valid for the chips that are fabricated in the same technology and design-style as the one from which the parameters were estimated. For finer features, one would expect the average number  $c$  of logical faults per physical defect to be larger and in that case equation (12) will give a lower fault coverage requirement for the same given reject ratio.

Normally, the yield equation is characterized by fitting (10) to the experimental data on yield versus area obtained from several chips of varying areas. In our analysis the characterization of the yield equation is accomplished from the data on just one type of chips. This is not surprising because the measured rejected fraction (or 1-yield),  $P(f)$  given by (9), contains the effect of yield variation as the tested area of chip increases.

To illustrate this we use (11) and rewrite (9) as

$$P(f) = 1 - [1 + A_f\bar{D}(\sigma/\mu)^2]^{-(\mu/\sigma)^2}$$

where  $A_f$  is the tested area given by

$$A_f = A \cdot \frac{1 - e^{-cf}}{1 - e^{-c}}.$$

Thus the  $P(f)$  versus  $f$  relation can also be thought of as 1-yield versus tested area. Notice that  $A_f$  is a nonlinear function of  $f$  since in our model, a defect can cause several faults. The special case of a single fault per defect can be analyzed by assuming  $c \ll 1$  so that the probability of more than one fault is very small. In this case  $A_f = Af$  as has been discussed in [11].

### V. CONCLUSION

Traditionally chip failure data has been used just to identify good chips from the bad ones. We have shown that such data, in combination with results from a fault simulator, can be used also to characterize important aspects of processing and testing. The yield equation derived in this paper is based on the distinction between physical defects and logical faults. The parameters of this equation are derived from the wafer-level test data.

Briefly, the advantages of the proposed approach are as follows:

- (1) Since the yield equation is characterized at the functional test level, it is capable of taking the technology-dependent factors into account.
- (2) No additional effort is required for data collection since the wafer-level tests for both yield characterization and production testing are the same.
- (3) The results of analysis may be used differently for a new and mature process. For a new process the parameters of the yield equation may be monitored closely for an unexpected deviation from the norm and used to raise an alert in case of such a deviation. For a mature process, the yield equation could be used to estimate the yield and the required fault coverage of a future chip with a different area.

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# Chip Substrate Resistance Modeling Technique for Integrated Circuit Design

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**Abstract**—With the advent of VLSI and the use of statistical simulation techniques to perform integrated circuit design, modeling of chip substrate resistance is becoming increasingly important to successful chip design. This paper will present a substrate resistance modeling technique which may be applied to the design of both FET and bipolar chips. After briefly presenting the theory behind the technique, we will describe its use in developing a substrate resistance model required for studying a disturb problem encountered with a high-speed array chip. The steps involved in building and simplifying the substrate model will be described. The effect on circuit simulations and noise sensitivity will then be shown.

## I. INTRODUCTION

THERE HAS BEEN an increasing need for accurate chip substrate modeling, particularly due to the use of high-resistivity substrates, low-power, disturb-sensitive Random

Access Memory (RAM) cells, and densely-packed VLSI designs. The need to understand substrate current and voltage distributions for FET charge storage dynamic RAM chips has existed for many years, in fact. More recently, low-power bipolar memory cell designs used for buffer applications have also required a study of substrate noise current induced by capacitive coupling from subcollector-isolation junctions.

In 1971, the IBM Components Division in East Fishkill, NY undertook a study to predict the substrate current and voltage waveforms for an 8K-bit dynamic FET RAM [1]. The approach taken was to represent the chip substrate as a large two-dimensional (2-D) matrix of resistors with distributed capacitance coupling due to switching row lines in the design. Circuit analysis was then performed with the ASTAP circuit simulation program [2] to study coupled voltage at various points within the chip and the overall induced substrate current.

In 1974 a problem was encountered in the bipolar logic chip design where it was necessary to study the distribution of cur-

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